UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO.

: 6,844,203 B2

DATED

: January 18, 2005

INVENTOR(S) : Ahn et al.

Page 1 of 2

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page, Item [54] and Column 1, line 1,

Title, after "OXIDES" delete ","

Title page,

Item [56], References Cited, OTHER PUBLICATIONS,

"Liu, Y. C.," reference, delete "plamsa" and insert -- plasma --, therefor.

"Qi, Wen-Jie, et al.," reference, delete "Cr02" and insert -- ZrO2 --, therefor.

"Aarik, Jaan, et al.," (third occurrence) delete "doposition" and insert -- deposition --, therefor.

"Ahn, K. Y., et al.," reference, delete "Dielectic" and insert -- Dielectric --, therefor.

"Alen, Petra," reference, after "as" insert -- a --.

"Bunshah, Rointan F., et al.," reference, delete "M.J." and insert -- N.J. --, therefor.

"Desu, S.B.," reference, delete "Fatique" and insert -- Fatigue --, therefor.

"Giess, E. A., et al.," reference, delete "Lathanide" and insert -- Lanthanide --, therefor.

"Guo, et al.," reference, delete "fo r" and insert -- for --, therefor; and delete "Ctied" and insert -- Cited --, therefor.

"Gusev, E P., et al.," reference, delete "Al203" and insert -- Al2O3 --, therefor.

"Kim, D., et al.," reference, delete "Subsrate" and insert -- Substrate --, therefor.

"Lee, et al.," reference, delete "fo rAlternative" and insert -- for Alternative --, therefor; and delete "Gae Dielecric" and insert -- Gate Dielectric --, therefor.

"Lou, Z J., et al.," reference, delete "GAte" and insert -- Gate --, therefor.

"Molodyk, A. A., et al.," reference, delete "Depostion" and insert -- Deposition --, therefor.

"Nakagawara, Osamu, et al.," reference, delete "films" and insert -- film --, therefor.

"Park, Jachoo, et al.," reference, delete "Soceity" and insert -- Society --, therefor.

"Poveshchenko, V P., et al.," reference, delete "phas" and insert -- phase --, therefor.

"Shanware, A, et al.," reference, delete "a" and insert -- A --, therefor.

"Tavel, B, et al.," reference, delete "419" and insert -- 429 --, therefor.

"Yamaguchi, Takeshi, et al.," reference, delete "FAbricated" and insert -- Fabricated --, therefor.

"Zhu, W, et al.," reference, delete "Tranport" and insert -- Transport --, therefor.

Column 1,

Line 58, delete "nM" and insert -- nm --, therefor.

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Page 2 of 2

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It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 4,

Line 29, delete "horizonal" and insert -- horizontal --, therefor.

Signed and Sealed this

Twenty-fourth Day of May, 2005

JON W. DUDAS
Director of the United States Patent and Trademark Office